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hydrogenated amorphous silicon germanium solar cells**

Duy Phong Pham¹, Sangho Kim², Jinjoo Park¹, Anh Huy Tuan Le¹, Jaehyun Cho², and Junsin Yi^{1,*}

¹ College of Information and Communication Engineering, Sungkyunkwan University, Suwon 440-746, Republic of Korea

² Department of Energy Science, Sungkyunkwan University, Suwon 440-746, Republic of Korea

***Corresponding author: Junsin Yi**

E-mail: yi@yurim.skku.ac.kr,

Tel.: +82-31-290 7139,

Fax.: +82-31-290 7139

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